



## **IRFL9014TRPBF Information**



For Reference Only

Part NumberIRFL9014TRPBFManufacturerVishay Siliconix

Category Discrete Semiconductor Products

Transistors - FETs, MOSFETs - Single

**Description** MOSFET P-CH 60V 1.8A SOT223

Package TO-261-4, TO-261AA

For the pricing/inventory/lead time, please contact

us

Website: https://www.heisener.com E-mail: salesdept@heisener.com



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# **Certified Quality**

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# **IRFL9014TRPBF Specifications**

Manufacturer Part Number         IRFL9014TRPBF           Manufacturer         Vishay Siliconix           Category         Discrete Semiconductor Products           Transistors - FETs, MOSFETs - Single           Package         TO-261-4, TO-261AA           Series         -           FET Type         P-Channel           Technology         MOSFET (Metal Oxide)           Drain to Source Voltage (Vdss)         60V           Current - Continuous Drain (Id) @ 25°C         1.8A (Tc)           Drive Voltage (Max Rds On, Min Rds On)         10V           Vgs(th) (Max) @ Id         4V @ 250µA           Gate Charge (Qg) (Max) @ Vgs         12nC @ 10V           Input Capacitance (Ciss) (Max) @ Vds         270pF @ 25V           Vgs (Max)         ±20V           FET Feature         -           Power Dissipation (Max)         2W (Ta), 3.1W (Tc)           Rds On (Max) @ Id, Vgs         500 mOhm @ 1.1A, 10V           Operating Temperature         -55°C ~ 150°C (TJ)           Mounting Type         Surface Mount           Supplier Device Package         SOT-223           Package / Case         TO-261-4, TO-261AA           Report errors?		
Category  Discrete Semiconductor Products  Transistors - FETs, MOSFETs - Single  Package  TO-261-4, TO-261AA  Series  - FET Type  P-Channel  Technology  Drain to Source Voltage (Vdss)  Current - Continuous Drain (Id) @ 25°C  Drive Voltage (Max Rds On, Min Rds On)  Vgs(th) (Max) @ Id  Gate Charge (Qg) (Max) @ Vgs  Input Capacitance (Ciss) (Max) @ Vds  270pF @ 25V  Vgs (Max)  FET Feature  Power Dissipation (Max)  Rds On (Max) @ Id, Vgs  Surface Mount  Supplier Device Package  Package / Case  TO-261-4, TO-261AA	Manufacturer Part Number	IRFL9014TRPBF
Package         TO-261-4, TO-261AA           Series         -           FET Type         P-Channel           Technology         MOSFET (Metal Oxide)           Drain to Source Voltage (Vdss)         60V           Current - Continuous Drain (Id) @ 25°C         1.8A (Tc)           Drive Voltage (Max Rds On, Min Rds On)         10V           Vgs(th) (Max) @ Id         4V @ 250μA           Gate Charge (Qg) (Max) @ Vgs         12nC @ 10V           Input Capacitance (Ciss) (Max) @ Vds         270pF @ 25V           Vgs (Max)         ±20V           FET Feature         -           Power Dissipation (Max)         2W (Ta), 3.1W (Tc)           Rds On (Max) @ Id, Vgs         500 mOhm @ 1.1A, 10V           Operating Temperature         -55°C ~ 150°C (TJ)           Mounting Type         Surface Mount           Supplier Device Package         SOT-223           Package / Case         TO-261-4, TO-261AA	Manufacturer	Vishay Siliconix
Package         TO-261-4, TO-261AA           Series         -           FET Type         P-Channel           Technology         MOSFET (Metal Oxide)           Drain to Source Voltage (Vdss)         60V           Current - Continuous Drain (Id) @ 25°C         1.8A (Tc)           Drive Voltage (Max Rds On, Min Rds On)         10V           Vgs(th) (Max) @ Id         4V @ 250μA           Gate Charge (Qg) (Max) @ Vgs         12nC @ 10V           Input Capacitance (Ciss) (Max) @ Vds         270pF @ 25V           Vgs (Max)         ±20V           FET Feature         -           Power Dissipation (Max)         2W (Ta), 3.1W (Tc)           Rds On (Max) @ Id, Vgs         500 mOhm @ 1.1A, 10V           Operating Temperature         -55°C ~ 150°C (TJ)           Mounting Type         Surface Mount           Supplier Device Package         SOT-223           Package / Case         TO-261-4, TO-261AA	Category	Discrete Semiconductor Products
Series         -           FET Type         P-Channel           Technology         MOSFET (Metal Oxide)           Drain to Source Voltage (Vdss)         60V           Current - Continuous Drain (Id) @ 25°C         1.8A (Tc)           Drive Voltage (Max Rds On, Min Rds On)         10V           Vgs(th) (Max) @ Id         4V @ 250µA           Gate Charge (Qg) (Max) @ Vgs         12nC @ 10V           Input Capacitance (Ciss) (Max) @ Vds         270pF @ 25V           Vgs (Max)         ±20V           FET Feature         -           Power Dissipation (Max)         2W (Ta), 3.1W (Tc)           Rds On (Max) @ Id, Vgs         500 mOhm @ 1.1A, 10V           Operating Temperature         -55°C ~ 150°C (TJ)           Mounting Type         Surface Mount           Supplier Device Package         SOT-223           Package / Case         TO-261-4, TO-261AA		Transistors - FETs, MOSFETs - Single
FET TypeP-ChannelTechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)60VCurrent - Continuous Drain (Id) @ 25°C1.8A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id4V @ 250μAGate Charge (Qg) (Max) @ Vgs12nC @ 10VInput Capacitance (Ciss) (Max) @ Vds270pF @ 25VVgs (Max)±20VFET Feature-Power Dissipation (Max)2W (Ta), 3.1W (Tc)Rds On (Max) @ Id, Vgs500 mOhm @ 1.1A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeSurface MountSupplier Device PackageSOT-223Package / CaseTO-261-4, TO-261AA	Package	TO-261-4, TO-261AA
TechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)60VCurrent - Continuous Drain (Id) @ 25°C1.8A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id4V @ 250μAGate Charge (Qg) (Max) @ Vgs12nC @ 10VInput Capacitance (Ciss) (Max) @ Vds270pF @ 25VVgs (Max)±20VFET Feature-Power Dissipation (Max)2W (Ta), 3.1W (Tc)Rds On (Max) @ Id, Vgs500 mOhm @ 1.1A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeSurface MountSupplier Device PackageSOT-223Package / CaseTO-261-4, TO-261AA	Series	-
Drain to Source Voltage (Vdss)60VCurrent - Continuous Drain (Id) @ 25°C1.8A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id4V @ 250μAGate Charge (Qg) (Max) @ Vgs12nC @ 10VInput Capacitance (Ciss) (Max) @ Vds270pF @ 25VVgs (Max)±20VFET Feature-Power Dissipation (Max)2W (Ta), 3.1W (Tc)Rds On (Max) @ Id, Vgs500 mOhm @ 1.1A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeSurface MountSupplier Device PackageSOT-223Package / CaseTO-261-4, TO-261AA	FET Type	P-Channel
Current - Continuous Drain (Id) @ 25°C  Drive Voltage (Max Rds On, Min Rds On)  Vgs(th) (Max) @ Id  Gate Charge (Qg) (Max) @ Vgs  12nC @ 10V  Input Capacitance (Ciss) (Max) @ Vds  270pF @ 25V  Vgs (Max)  ±20V  FET Feature  - Power Dissipation (Max)  Rds On (Max) @ Id, Vgs  500 mOhm @ 1.1A, 10V  Operating Temperature  Supplier Device Package  Package / Case  1.8A (Tc)  1.8  4. V @ 250µA  2. V (Ta)  1.1A (10V)  1.1A (10V	Technology	MOSFET (Metal Oxide)
Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id4V @ 250μAGate Charge (Qg) (Max) @ Vgs12nC @ 10VInput Capacitance (Ciss) (Max) @ Vds270pF @ 25VVgs (Max)±20VFET Feature-Power Dissipation (Max)2W (Ta), 3.1W (Tc)Rds On (Max) @ Id, Vgs500 mOhm @ 1.1A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeSurface MountSupplier Device PackageSOT-223Package / CaseTO-261-4, TO-261AA	Drain to Source Voltage (Vdss)	60V
Vgs(th) (Max) @ Id  Gate Charge (Qg) (Max) @ Vgs  Input Capacitance (Ciss) (Max) @ Vds  Vgs (Max)  FET Feature  Power Dissipation (Max)  As Son (Max) @ Id, Vgs  Operating Temperature  Supplier Device Package  Package / Case  4V @ 250μA  12nC @ 10V  270pF @ 25V  +20V  FET (Pe 25V  -20V  FET Feature  -20V  FET Feature  -30V  FET Feature  -40V  -50V  -50	Current - Continuous Drain (Id) @ 25°C	1.8A (Tc)
Gate Charge (Qg) (Max) @ Vgs  Input Capacitance (Ciss) (Max) @ Vds  270pF @ 25V  Vgs (Max)  ±20V  FET Feature  - Power Dissipation (Max)  Rds On (Max) @ Id, Vgs  500 mOhm @ 1.1A, 10V  Operating Temperature  -55°C ~ 150°C (TJ)  Mounting Type  Surface Mount  Supplier Device Package  Package / Case  TO-261-4, TO-261AA	Drive Voltage (Max Rds On, Min Rds On)	10V
Input Capacitance (Ciss) (Max) @ Vds  270pF @ 25V  Vgs (Max)  E20V  FET Feature  - Power Dissipation (Max)  Rds On (Max) @ Id, Vgs  500 mOhm @ 1.1A, 10V  Operating Temperature  -55°C ~ 150°C (TJ)  Mounting Type  Surface Mount  Supplier Device Package  SOT-223  Package / Case  TO-261-4, TO-261AA	Vgs(th) (Max) @ Id	4V @ 250μA
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Power Dissipation (Max)  Rds On (Max) @ Id, Vgs  500 mOhm @ 1.1A, 10V  Operating Temperature  -55°C ~ 150°C (TJ)  Mounting Type  Surface Mount  Supplier Device Package  SOT-223  Package / Case  TO-261-4, TO-261AA	Vgs (Max)	±20V
Rds On (Max) @ Id, Vgs500 mOhm @ 1.1A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeSurface MountSupplier Device PackageSOT-223Package / CaseTO-261-4, TO-261AA	FET Feature	-
Operating Temperature  -55°C ~ 150°C (TJ)  Mounting Type  Surface Mount  Supplier Device Package  SOT-223  Package / Case  TO-261-4, TO-261AA	Power Dissipation (Max)	2W (Ta), 3.1W (Tc)
Mounting Type Surface Mount Supplier Device Package SOT-223 Package / Case TO-261-4, TO-261AA	Rds On (Max) @ Id, Vgs	500 mOhm @ 1.1A, 10V
Supplier Device Package SOT-223 Package / Case TO-261-4, TO-261AA	Operating Temperature	-55°C ~ 150°C (TJ)
Package / Case TO-261-4, TO-261AA	Mounting Type	Surface Mount
	Supplier Device Package	SOT-223
Report errors?	Package / Case	TO-261-4, TO-261AA
		Report errors?

#### **IRFL9014TRPBF** Guarantees



#### **Quality Guarantees**

We provide 90 days warranty. \*

If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.



#### **Service Guarantees**

We guarantee 100% customer satisfaction.

Our experienced sales team and tech support team back our services to satisfy all our customers.

### **IRFL9014TRPBF Payment Methods**



















### **IRFL9014TRPBF Shipping Methods**













If you have any question about IRFL9014TRPBF, please do not hesitate to contact us!

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